SHE)F

INFORMATION DISCLOSURE			ATTY. DOCKET NO. 57810-077							
CITATION IN AN APPLICATION										
AN 2 8 2004			APPLICANT Yasuhiko NOMURA, et al.							
(PTO-1449)			FILING DATE September 17, 2003	FILING DATE GROUP September 17, 2003 2828						
NOEW N	· · · ·	· 一个一个一个	U.S. PATEN	IT DOCUMENTS	£ 15					
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (7 known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Pages, Columns, Lines, Passages or Relevant						
		US								
		US								
		US		·			····			
	-	US			 		· · · · · · · · · · · · · · · · · · ·			
		US								
		US	<u> </u>							
ļ	 	US								
<u> </u>		US	 				$\overline{}$			
- 700 E Sec.	** **	2 2 2 3	FOREIGN:PA	TENT DOCUMENTS :		3 4 2 1 1	· Carlet			
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (If known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document Pages, Columns, Lines Where Relevant Figures Appear						
			<u></u>			Yes	No			
an G		JP 2002-124737	04/26/2002	SANYO ELECTRIC CO LTD	·	JAPAN (w/English Abstract)				
MG		JP 2002-299768	10/11/2002	MATSUSHITA ELECTRIC IND CO LTD	_	JAPAN (w/English Abstract)				
mG		JP 2001-57461	02/27/2001	NICHIA CHEM IND LTD		JAPAN (w/English Abstract)				
MG		JP 11-340580	12/10/1999	FUJITSU LTD		JAPAN (w/English Abstract)				
m G		JP 10-294529	11/4/1998	TOSHIBA CORP.		JAPAN (w/English Abstract)				
"是"	梦梦			or, Title, Date, Pertinent Pages, Etc.		4 5 6 2 3	A de s			
EXAMINER'S INITIALS	CITE NO.	Include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.								
M6		Nishinaga Tatau, "Hetero-epitaxy with Large Lattice Mismatch and Microchannel Epitaxy of Compound Semiconductor." Department of Electronic Engineering, Graduate School of Engineering, Volume 21, No. 8, pp. 320-325, 2000								
716		H. Amano, et al. " Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AIN buffer layer." Appl. Phys. Lett., Vol. 48, No. 5, 3 February 1986. pp. 353-355								
Maria Gold 08/17/2005										

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.